

Bipolar Power Transistors

40 V, 3.0 A, Low $V_{CE(sat)}$

NPN Transistor

NSS40301MZ4

onsemi's e²PowerEdge family of low $V_{CE(sat)}$ transistors are surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

Features

- Complement to NSS40300MZ4 Series
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CB}	40	Vdc
Emitter-Base Voltage	V_{EB}	6.0	Vdc
Base Current - Continuous	I_B	1.0	Adc
Collector Current - Continuous	I_C	3.0	Adc
Collector Current - Peak	I_{CM}	5.0	Adc
Total Power Dissipation Total P_D @ $T_A = 25^\circ\text{C}$ (Note 1) Total P_D @ $T_A = 25^\circ\text{C}$ (Note 2)	P_D	2.0 0.80	W
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

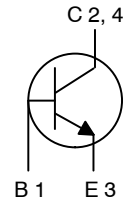
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Mounted on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material.
2. Mounted on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material.

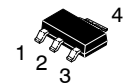
NPN TRANSISTOR

3.0 AMPERES

40 VOLTS, 2.0 WATTS

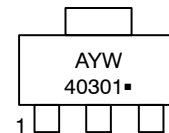


Schematic



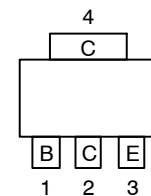
SOT-223
CASE 318E
STYLE 1

MARKING DIAGRAM



- A = Assembly Location
Y = Year
W = Work Week
40301 = Specific Device Code
■ = Pb-Free Package

PIN ASSIGNMENT



Top View Pinout

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NSS40301MZ4

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material Junction-to-Ambient on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material	$R_{\theta JA}$ $R_{\theta JA}$	64 155	$^{\circ}C/W$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T_L	260	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage ($I_C = 10$ mAdc, $I_B = 0$ Adc)	$V_{CEO(sus)}$	40	-	-	Vdc
Emitter-Base Voltage ($I_E = 50$ μ Adc, $I_C = 0$ Adc)	V_{EBO}	6.0	-	-	Vdc
Collector Cutoff Current ($V_{CB} = 40$ Vdc)	I_{CBO}	-	-	100	nAdc
Emitter Cutoff Current ($V_{BE} = 6.0$ Vdc)	I_{EBO}	-	-	100	nAdc

ON CHARACTERISTICS (Note 3)

Collector-Emitter Saturation Voltage ($I_C = 0.5$ Adc, $I_B = 50$ mAdc) ($I_C = 1.0$ Adc, $I_B = 20$ mAdc) ($I_C = 3.0$ Adc, $I_B = 0.3$ Adc)	$V_{CE(sat)}$	- - -	- - -	0.050 0.100 0.200	Vdc
Base-Emitter Saturation Voltage ($I_C = 1.0$ Adc, $I_B = 0.1$ Adc)	$V_{BE(sat)}$	-	-	1.0	Vdc
Base-Emitter On Voltage ($I_C = 1.0$ Adc, $V_{CE} = 2.0$ Vdc)	$V_{BE(on)}$	-	-	0.9	Vdc
DC Current Gain ($I_C = 0.5$ Adc, $V_{CE} = 1.0$ Vdc) ($I_C = 1.0$ Adc, $V_{CE} = 1.0$ Vdc) ($I_C = 3.0$ Adc, $V_{CE} = 1.0$ Vdc)	h_{FE}	220 200 100	- - -	500	-

DYNAMIC CHARACTERISTICS

Output Capacitance ($V_{CB} = 10$ Vdc, $f = 1.0$ MHz)	C_{ob}	-	25	-	pF
Input Capacitance ($V_{EB} = 5.0$ Vdc, $f = 1.0$ MHz)	C_{ib}	-	170	-	pF
Current-Gain - Bandwidth Product (Note 4) ($I_C = 500$ mA, $V_{CE} = 10$ V, $F_{test} = 1.0$ MHz)	f_T	-	215	-	MHz

3. Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle $\leq 2\%$.

4. $f_T = |h_{FE}| \cdot f_{test}$

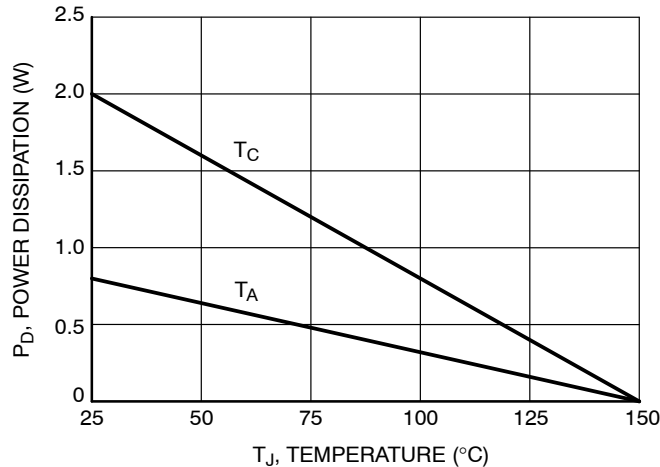


Figure 1. Power Derating

NSS40301MZ4

TYPICAL CHARACTERISTICS

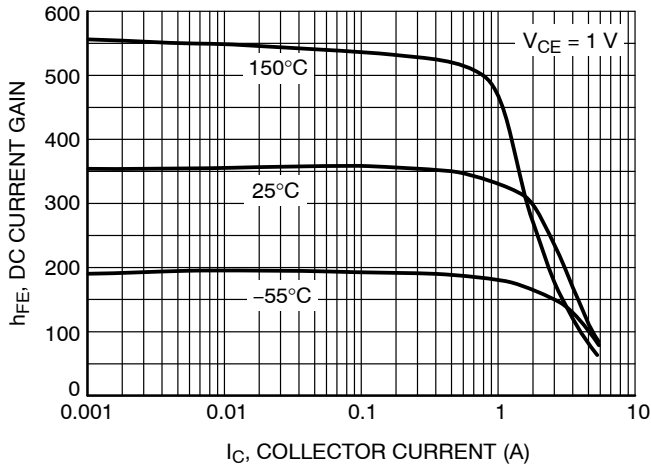


Figure 2. DC Current Gain

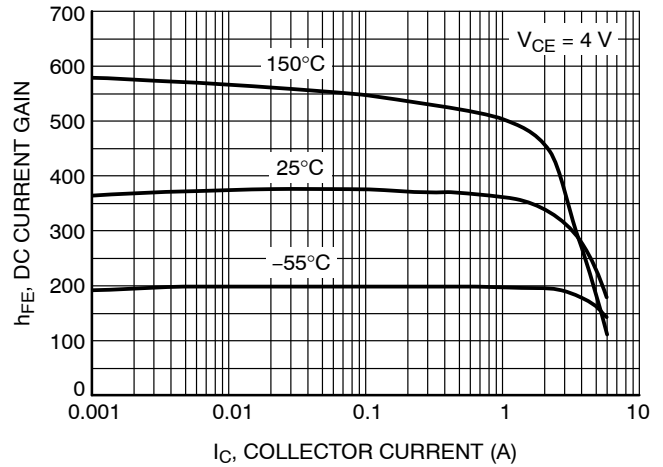


Figure 3. DC Current Gain

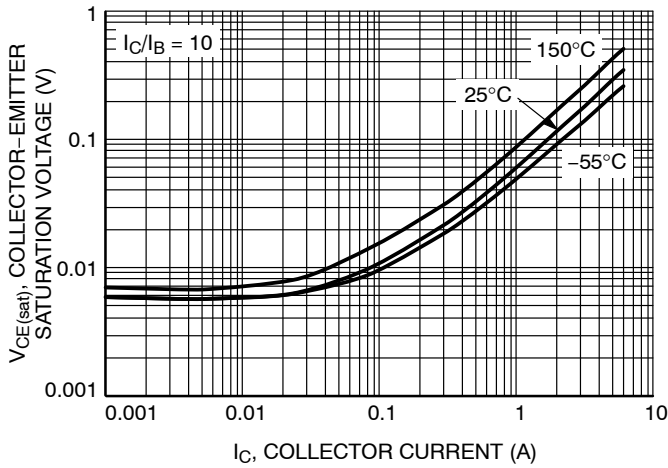


Figure 4. Collector-Emitter Saturation Voltage

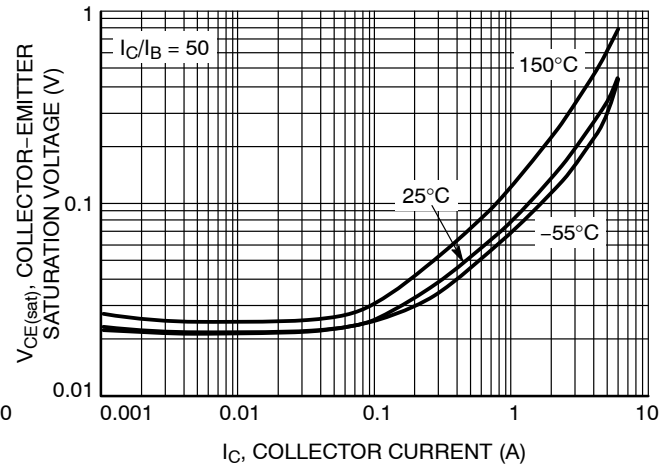


Figure 5. Collector-Emitter Saturation Voltage

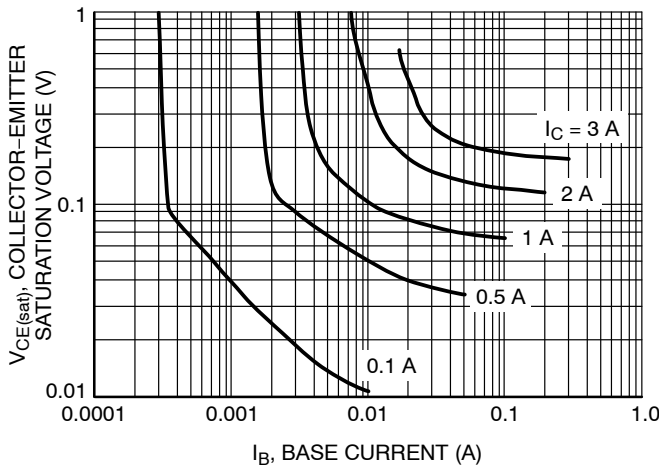


Figure 6. Collector Saturation Region

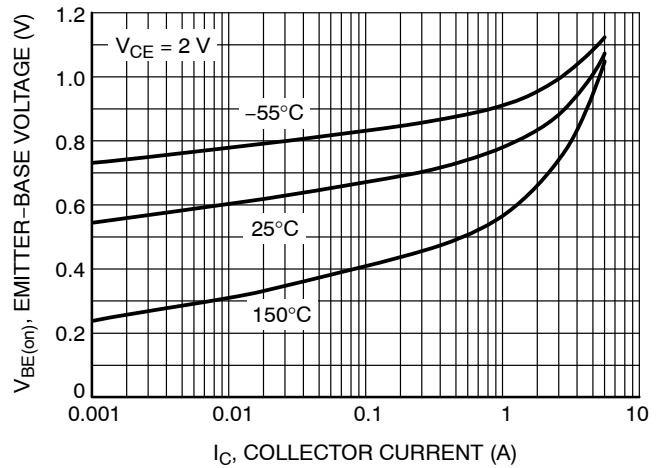


Figure 7. $V_{BE(on)}$ Voltage

NSS40301MZ4

TYPICAL CHARACTERISTICS

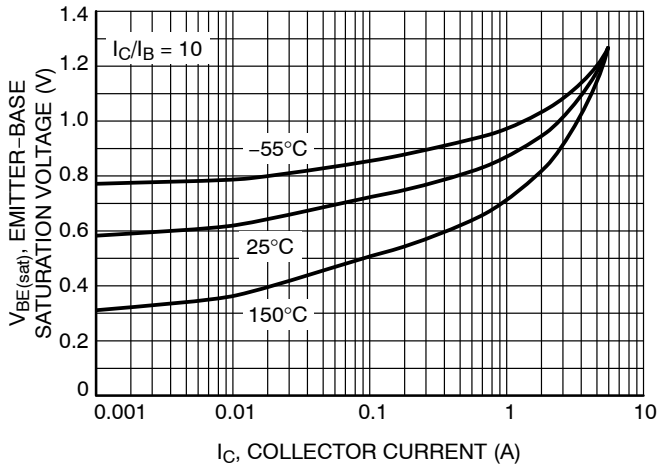


Figure 8. Base-Emitter Saturation Voltage

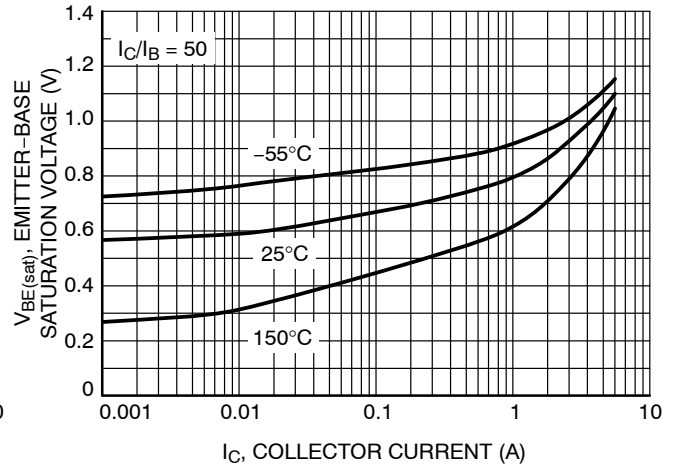


Figure 9. Base-Emitter Saturation Voltage

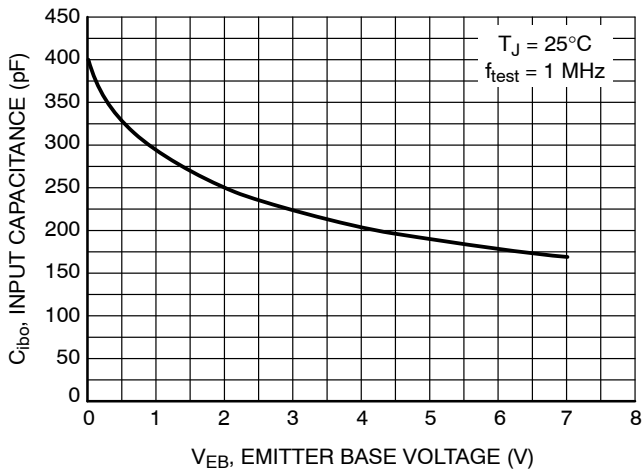


Figure 10. Input Capacitance

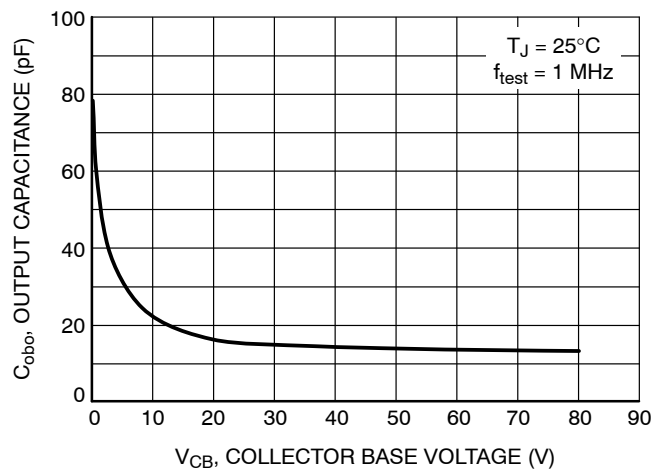


Figure 11. Output Capacitance

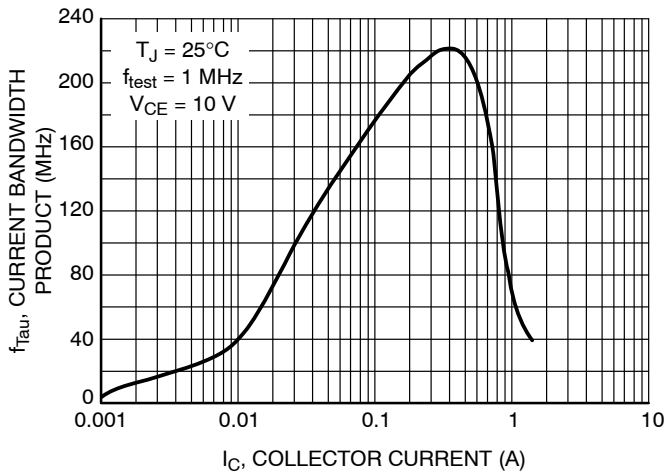


Figure 12. Current-Gain Bandwidth Product

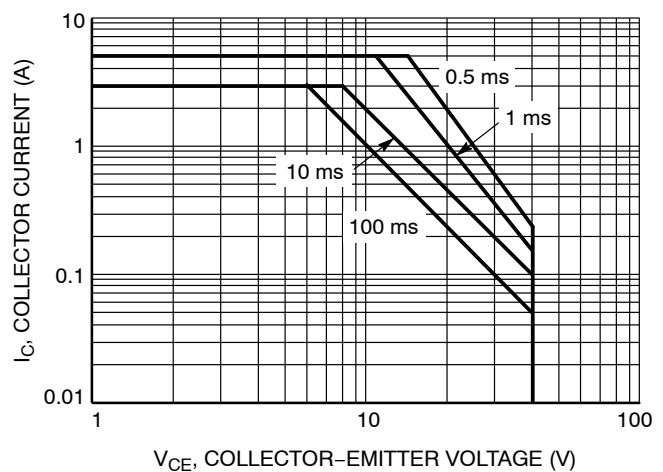


Figure 13. Safe Operating Area

NSS40301MZ4

ORDERING INFORMATION

Device	Package	Shipping [†]
NSS40301MZ4T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
NSV40301MZ4T1G*	SOT-223 (Pb-Free)	1,000 / Tape & Reel
NSS40301MZ4T3G	SOT-223 (Pb-Free)	4,000 / Tape & Reel
NSV40301MZ4T3G*	SOT-223 (Pb-Free)	4,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

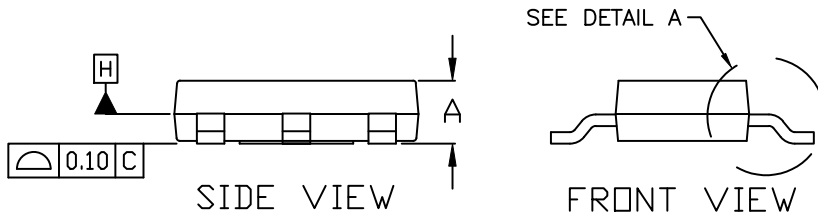
ON Semiconductor®



SCALE 1:1

SOT-223 (TO-261)
CASE 318E-04
ISSUE R

DATE 02 OCT 2018



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
c	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		
L	0.20	---	---
L1	1.50	1.75	2.00
He	6.70	7.00	7.30
θ	0°	---	10°



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SOT-223 (TO-261)
CASE 318E-04
ISSUE R

DATE 02 OCT 2018

- | | | | | |
|--|---|---|---|---|
| STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR | STYLE 2:
PIN 1. ANODE
2. CATHODE
3. NC
4. CATHODE | STYLE 3:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN | STYLE 4:
PIN 1. SOURCE
2. DRAIN
3. GATE
4. DRAIN | STYLE 5:
PIN 1. DRAIN
2. GATE
3. SOURCE
4. GATE |
| STYLE 6:
PIN 1. RETURN
2. INPUT
3. OUTPUT
4. INPUT | STYLE 7:
PIN 1. ANODE 1
2. CATHODE
3. ANODE 2
4. CATHODE | STYLE 8:
CANCELLED | STYLE 9:
PIN 1. INPUT
2. GROUND
3. LOGIC
4. GROUND | STYLE 10:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE |
| STYLE 11:
PIN 1. MT 1
2. MT 2
3. GATE
4. MT 2 | STYLE 12:
PIN 1. INPUT
2. OUTPUT
3. NC
4. OUTPUT | STYLE 13:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR | | |

**GENERIC
 MARKING DIAGRAM***




- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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